

● **General Description**

The TF30P02 combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

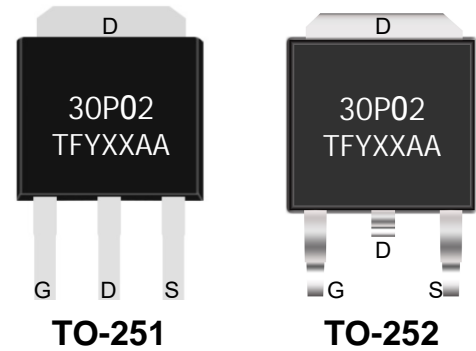
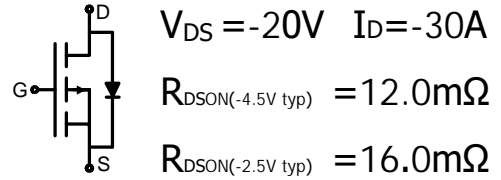
● **Features**

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

● **Application**

- Load Switches
- DC/DC
- BLDC Motor driver

● **Product Summary**



● **Ordering Information:**

Part NO.	TF30P02
Marking1	30N02:TF30P02
Marking2	TF:tuofeng; Y:year code; XX:Week; AA:device code;
Basic ordering unit (pcs)	2500

● **Absolute Maximum Ratings (T_c =25°C)**

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	-20	V
Gate-Source Voltage	V _{GS}	±12	V
Continuous Drain Current	I _{D@TC=25°C}	-30	A
	I _{D@TC=75°C}	-21	A
	I _{D@TC=100°C}	-18	A
Pulsed Drain Current ①	I _{DM}	-65	A
Total Power Dissipation ^②	P _D	15	W
Total Power Dissipation(TA=25°C)	P _{D@TA=25°C}	1.0	W
Operating Junction Temperature	T _J	-55 to 150	°C
Storage Temperature	T _{STG}	-55 to 150	°C
Single Pulse Avalanche Energy@L=0.1mH	E _{AS}	45	mJ
Avalanche Current@L=0.1mH	I _{AS}	-30	A



● **Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case ^②	R _{thJC}	-	-	4.5	° C/W
Thermal resistance, junction - ambient	R _{thJA}	-	-	62.5	° C/W
Soldering temperature, wave soldering for 10s	T _{sold}	-	-	265	° C

● **Electronic Characteristics**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = -250uA	-20			V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = -250uA	-0.45	-0.70	-1.00	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} = -20V, V _{GS} = 0V			-1.0	uA
Gate- Source Leakage Current	I _{GSS}	V _{GS} = ±12V, V _{DS} = 0V			±100	nA
Static Drain-source On Resistance	R _{DS(ON)}	V _{GS} = -4.5V, I _D = -15A		12.0	15.0	mΩ
		V _{GS} = -2.5V, I _D = -10A		16.0	20.0	mΩ
Forward Transconductance	g _{FS}	V _{DS} = -10V, I _D = -10A		10		s
Source-drain voltage	V _{SD}	I _S = -10A		0.88	1.28	V

● **Electronic Characteristics**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = -10V f = 1MHz	-	1545	-	pF
Output capacitance	C _{oss}		-	168.7	-	
Reverse transfer capacitance	C _{rss}		-	148.1	-	

● **Gate Charge characteristics**(T_a = 25°C)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q _g	V _{DD} = -10V	-	24.5	-	nC
Gate - Source charge	Q _{gs}	I _D = -10A	-	3.69	-	
Gate - Drain charge	Q _{gd}	V _{GS} = -4.5V	-	4.58	-	

Note: ① Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2% ;

② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;

Fig.1 Gate-Charge Characteristics

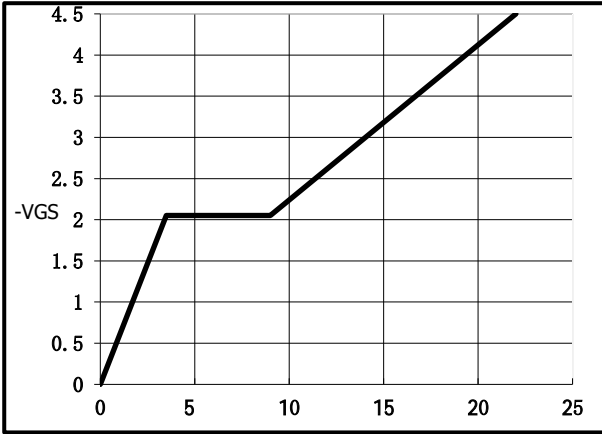


Fig.2 Capacitance Characteristics

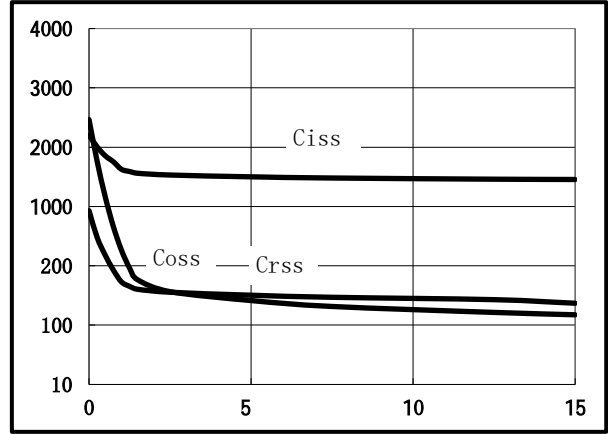


Fig.2 Power Dissipation

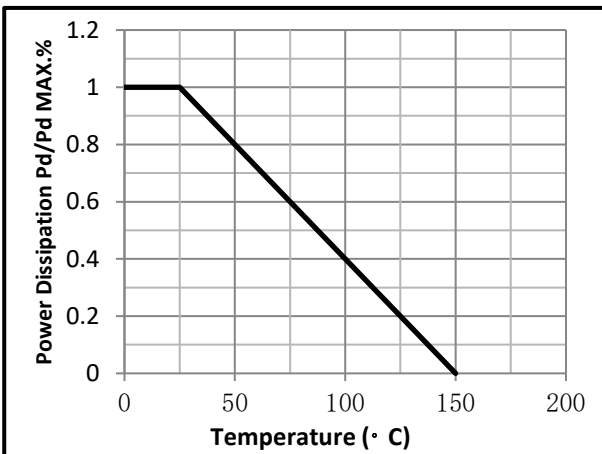


Fig.3 Typical output Characteristics

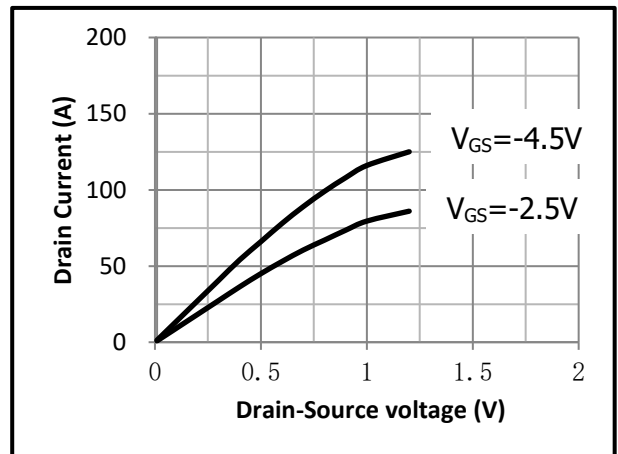


Fig.4 Threshold Voltage V.S Junction Temperature

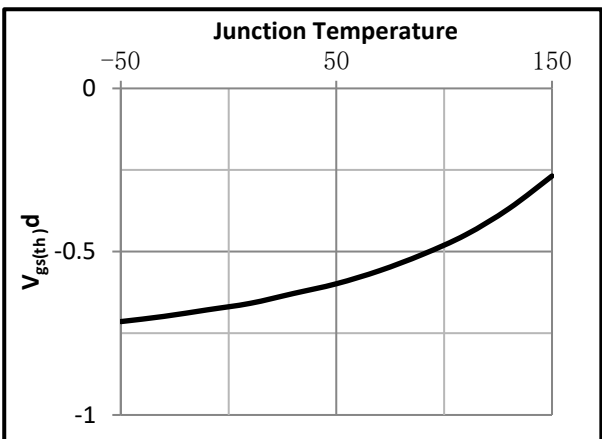


Fig.5 Resistance V.S Drain Current

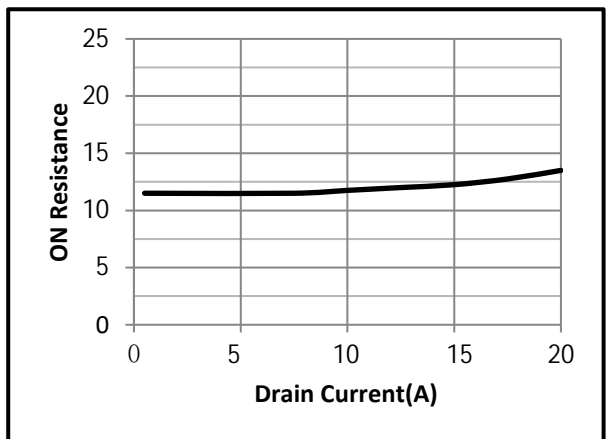


Fig.6 On-Resistance VS Gate Source Voltage

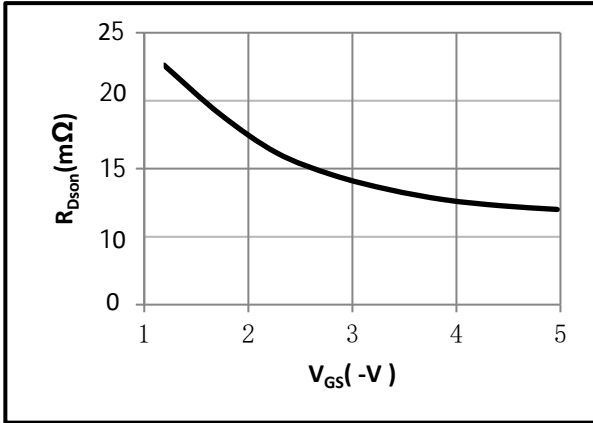


Fig.7 On-Resistance V.S Junction Temperature

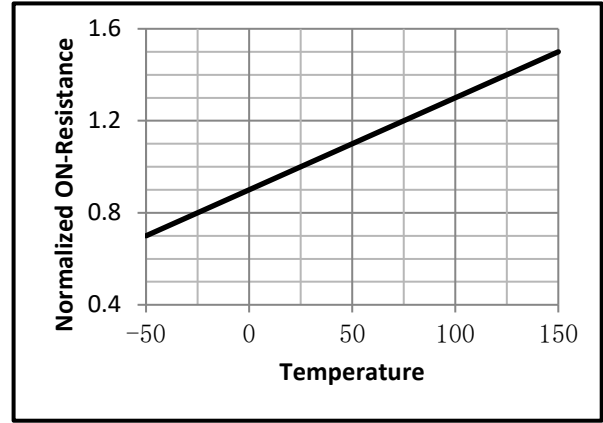


Fig.8 Switching Time Measurement Circuit

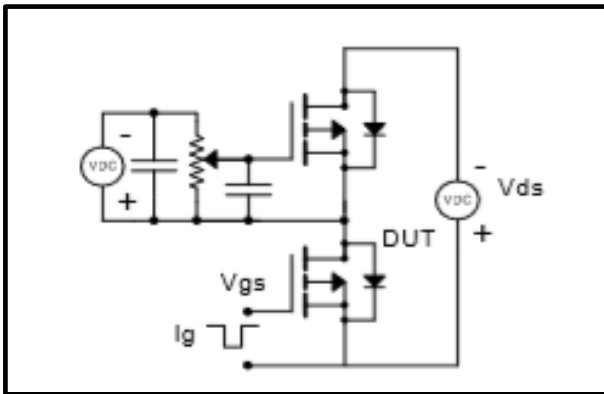


Fig.9 Gate Charge Waveform

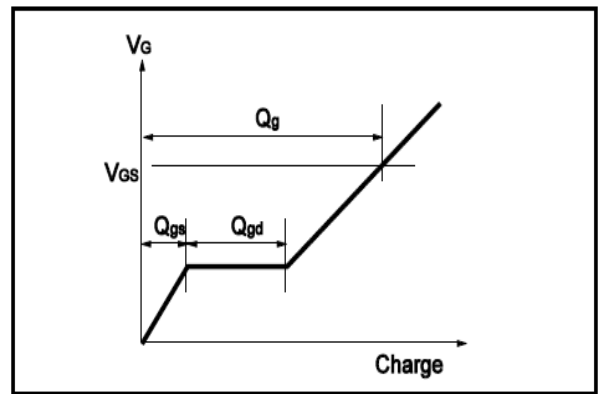


Fig.10 Switching Time Measurement Circuit

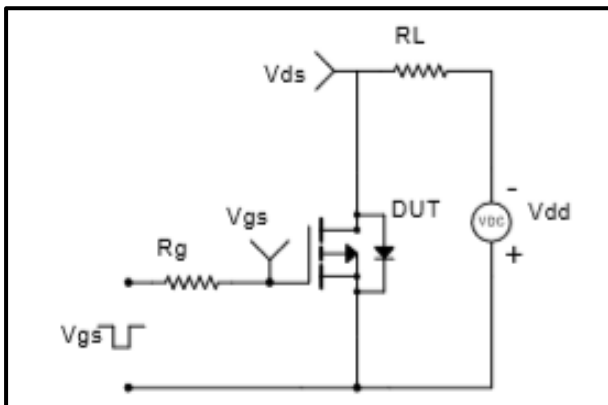
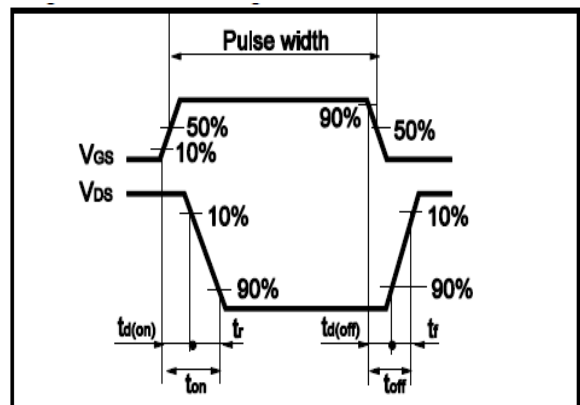
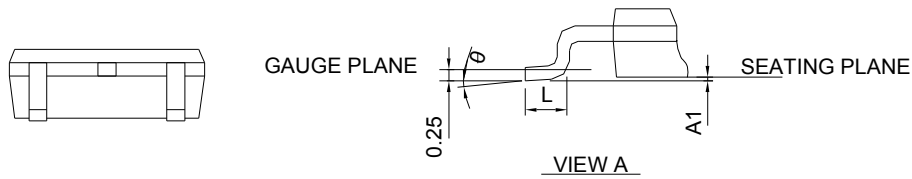
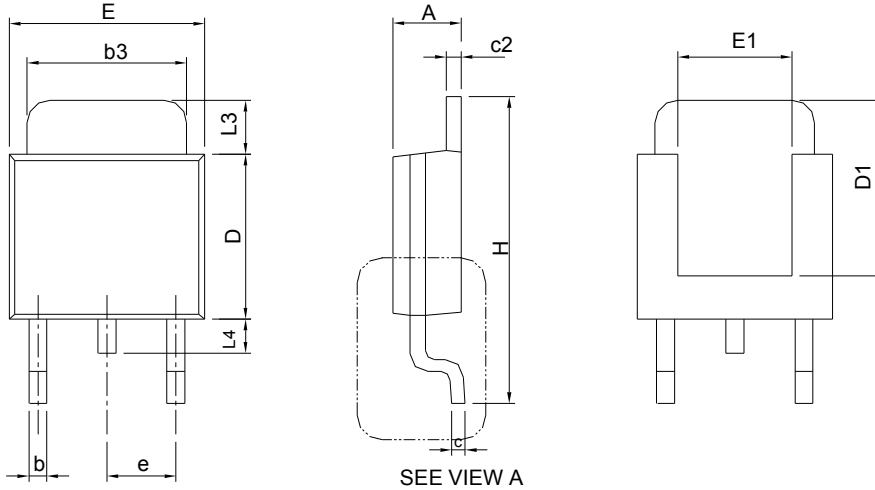


Fig.11 Gate Charge Waveform



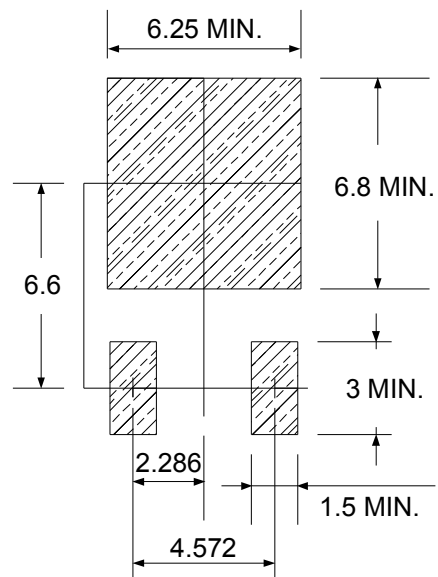
Package Information

TO-252



DIMENSIONS	TO-252			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.39	0.086	0.094
A1		0.13		0.005
b	0.50	0.89	0.020	0.035
b3	4.95	5.46	0.195	0.215
c	0.46	0.61	0.018	0.024
c2	0.46	0.89	0.018	0.035
D	5.33	6.22	0.210	0.245
D1	4.57	6.00	0.180	0.236
E	6.35	6.73	0.250	0.265
E1	3.81	6.00	0.150	0.236
e	2.29 BSC		0.090 BSC	
H	9.40	10.41	0.370	0.410
L	0.90	1.78	0.035	0.070
L3	0.89	2.03	0.035	0.080
L4		1.02		0.040
θ	0°	8°	0°	8°

RECOMMENDED LAND PATTERN



UNIT: mm